Switch-mode Power Rectifiers

These state-of-the-art devices are a series designed for use in switching power supplies, inverters and as free wheeling diodes.

Features

- Ultrafast 35 and 60 Nanosecond Recovery Time
- 175°C Operating Junction Temperature
- High Voltage Capability to 600 V
- ESD Ratings:
 - Machine Model = C
 - Human Body Model = 3B
- Low Forward Drop
- Low Leakage Specified @ 150°C Case Temperature
- Current Derating Specified @ Both Case and Ambient Temperatures
- SUR8 Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- All Packages are Pb-Free*

Mechanical Characteristics:

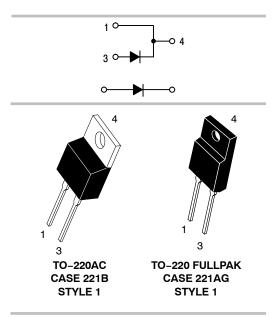
- Case: Epoxy, Molded
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds



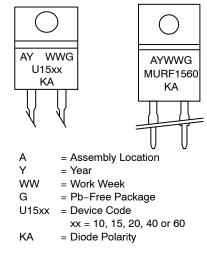
ON Semiconductor®

http://onsemi.com

ULTRAFAST RECTIFIERS 15 AMPERES, 100–600 VOLTS



MARKING DIAGRAMS



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 7 of this data sheet.

MAXIMUM RATINGS

		MUR/SUR8					
Rating	Symbol	1510	1515	1520	1540	1560	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _R	100	150	200	400	600	V
Average Rectified Forward Current (Rated V _R)	I _{F(AV)}	15 @ T _C = 150°C		15 @ T _C = 145°C	А		
Peak Rectified Forward Current (Rated V _R , Square Wave, 20 kHz)	I _{FRM}	30 @ T _C = 150°C		30 @ T _C = 145°C	А		
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I _{FSM}	200		150	A		
Operating Junction Temperature and Storage Temperature Range	T _J , T _{stg}	-65 to +175			°C		

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

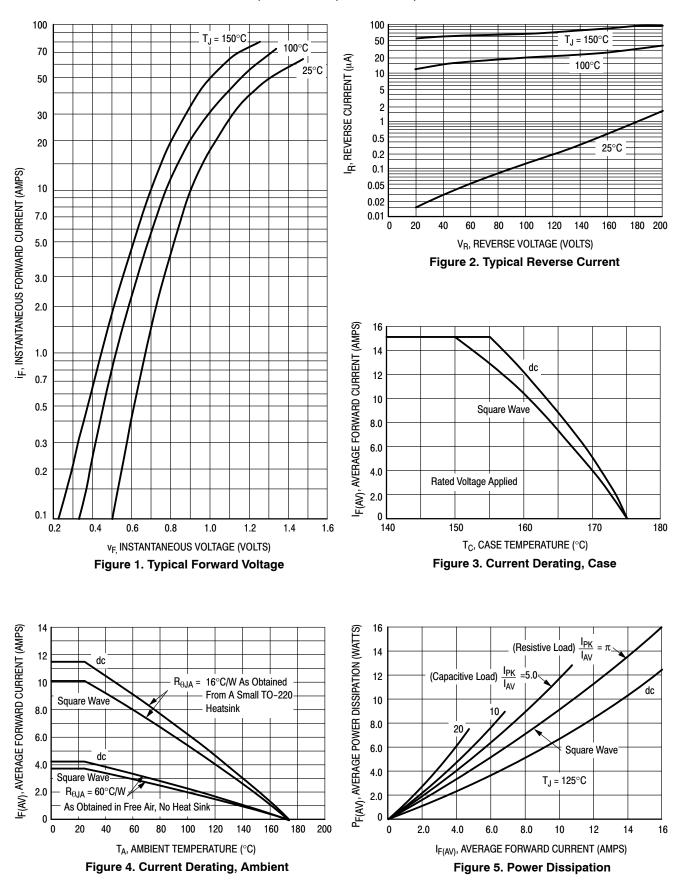
Characteristic	Symbol	Value	Unit
MUR1510 Series: Thermal Resistance Junction-to-Case Junction-to-Ambient	R _{θJC} R _{θJA}	1.5 73	°C/W
MURF1560: Thermal Resistance Junction-to-Case Junction-to-Ambient	${\sf R}_{ heta {\sf JC}} \ {\sf R}_{ heta {\sf JA}}$	4.25 75	°C/W

ELECTRICAL CHARACTERISTICS

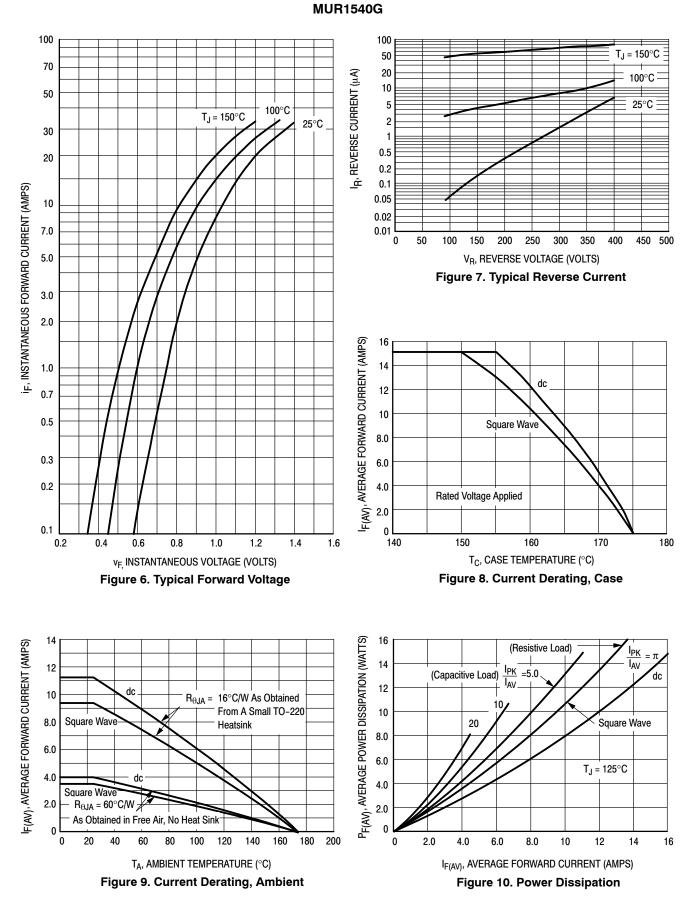
Characteristic	Symbol	1510	1515	1520	1540	1560	Unit
Maximum Instantaneous Forward Voltage (Note 1) (i _F = 15 A, T _C = 150°C) (i _F = 15 A, T _C = 25°C)	VF		0.85 1.05		1.12 1.25	1.20 1.50	V
Maximum Instantaneous Reverse Current (Note 1) (Rated DC Voltage, $T_C = 150^{\circ}C$) (Rated DC Voltage, $T_C = 25^{\circ}C$)	i _R		500 10		500 10	1000 10	μΑ
Maximum Reverse Recovery Time (I _F = 1.0 A, di/dt = 50 A/μs)	t _{rr}		35			60	ns

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

1. Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2.0%.



MUR1510G, MUR1515G, MUR1520G, SUR81520G



100 200 iF, INSTANTANEOUS FORWARD CURRENT (AMPS) 100 T_J = 150°C C 50 150 IR, REVERSE CURRENT (MA) 100°C 20 25°C 10 10 100°C 5 2 1 0.5 1 25°C 0.2 0.1 0.05 0.02 L 150 0.1 200 250 300 0.2 1.0 1.2 1.4 1.6 350 400 450 500 550 600 650 0.4 0.6 0.8 **v**_E INSTANTANEOUS VOLTAGE (VOLTS) V_R, REVERSE VOLTAGE (VOLTS) Figure 11. Typical Forward Voltage Figure 12. Typical Reverse Current I_{F(AV)}, AVERAGE FORWARD CURRENT (AMPS) 16 10 I_{F(AV)}, AVERAGE FORWARD CURRENT (AMPS) dc 9.0 14 dc 8.0 $R_{\theta JA} =$ 16°C/W As Obtained 12 Square Wave From A Small TO-220 7.0 Square Wave Heatsink 10 6.0 8.0 5.0 4.0 dc 6.0 3.0 4.0 Square Wave **Rated Voltage Applied** 2.0 $R_{\theta JA} = 60^{\circ}C/W$ 2.0 1.0 As Obtained in Free Air, No Heat Sink 0 0 160 170 180 160 200 140 150 20 60 100 120 140 180 0 40 80 T_C, CASE TEMPERATURE (°C) T_A, AMBIENT TEMPERATURE (°C) Figure 13. Current Derating, Case Figure 14. Current Derating, Ambient IFSM; NON-REPETITIVE SURGE CURRENT (A) 000'01 01 01 000'01 P_{F(AV)}, AVERAGE POWER DISSIPATION (WATTS) 16 I_{PK} =5.0 dc (Capacitive Load) 14 I_{A\} 10 12 10 20 Square Wave 8.0 $\frac{I_{PK}}{I_{PK}} = \pi$ 6.0 (Resistive-Inductive Load) IAV 4.0 T_J = 125°C 2.0 0 10 100 1,000 10,000 0 2.0 4.0 6.0 8.0 10 12 14 16 $t_{\text{p}},$ SQUARE WAVE PULSE DURATION (µs) IF(AV), AVERAGE FORWARD CURRENT (AMPS) Figure 16. Typical Non-Repetitive Surge Figure 15. Power Dissipation Current

MUR1560G, MURF1560G, SUR81560G

* Typical performance based on a limited sample size. ON Semiconductor does not guarantee ratings not listed in the Maximum Ratings table.

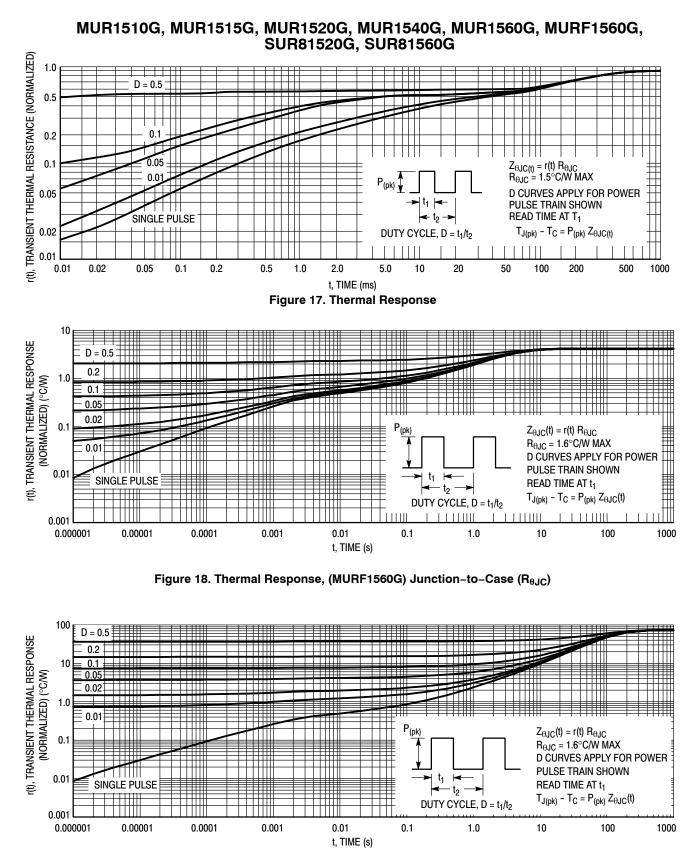


Figure 19. Thermal Response, (MURF1560G) Junction-to-Ambient ($R_{\theta JA}$)

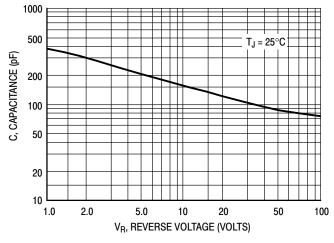


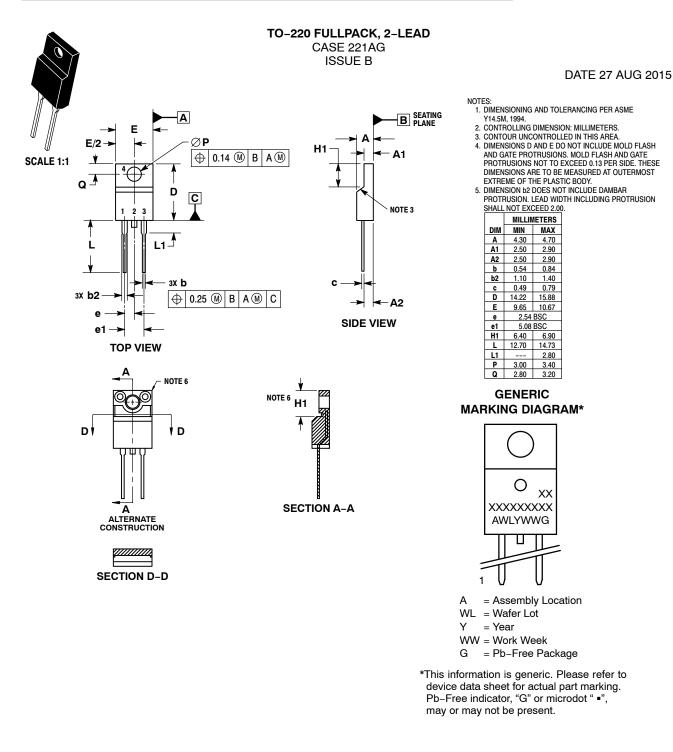
Figure 20. Typical Capacitance

ORDERING INFORMATION

Device	Package	Shipping [†]
MUR1510G	TO-220AC (Pb-Free)	50 Units / Rail
MUR1515G	TO-220AC (Pb-Free)	50 Units / Rail
MUR1520G	TO-220AC (Pb-Free)	50 Units / Rail
SUR81520G	TO-220AC (Pb-Free)	50 Units / Rail
MUR1540G	TO-220AC (Pb-Free)	50 Units / Rail
MUR1560G	TO-220AC (Pb-Free)	50 Units / Rail
SUR81560G	TO-220AC (Pb-Free)	50 Units / Rail
MURF1560G	TO-220FP (Pb-Free)	50 Units / Rail

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



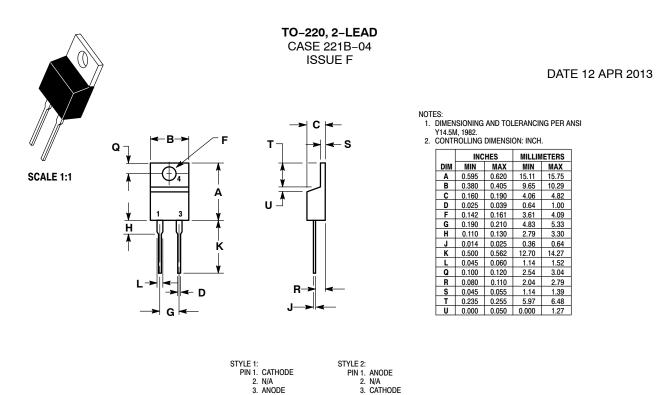


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 TO-220 FULLPACK, 2-LEAD
 PAGE 1 OF 1

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